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NTLUS4C12N

MOSFET – Power, Single, N-Channel, μCool, UDFN6, 2.0x2.0x0.55 mm
30 V, 10.7 A

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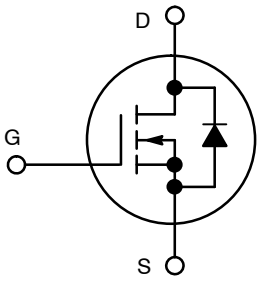
Features
- Low Profile UDFN 2.0 x 2.0 x 0.55 mm for Board Space Saving with Exposed Drain Pads for Excellent Thermal Conduction
- Ultra Low $R_{DS(on)}$ to Reduce Conduction Losses
- Optimized Gate Charge to Reduce Switching Losses
- Low Capacitance to Minimize Driver Losses
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Applications
- Power Load Switch
- Synch DC−DC Converters
- Wireless Charging Circuit

MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
30 V	9 mΩ @ 10 V	10.7 A
	12 mΩ @ 4.5 V	
	15 mΩ @ 3.7 V	
	19 mΩ @ 3.3 V	



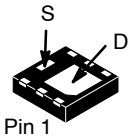
N−CHANNEL MOSFET

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	30	V
Gate-to-Source Voltage			V_{GS}	±20	V
Continuous Drain Current (Note 1)	Steady State	T_A = 25°C	I_D	10.7	A
		T_A = 85°C		7.7	
	t ≤ 5 s	T_A = 25°C		15.1	
Power Dissipation (Note 1)	Steady State	T_A = 25°C	P_D	1.54	W
	t ≤ 5 s	T_A = 25°C		3.1	
Continuous Drain Current (Note 2)	Steady State	T_A = 25°C	I_D	6.8	A
		T_A = 85°C		4.9	
Power Dissipation (Note 2)		T_A = 25°C	P_D	0.63	W
Pulsed Drain Current		t_p = 10 μs	I_{DM}	43	A
MOSFET Operating Junction and Storage Temperature			T_J, T_{STG}	-55 to 150	°C
Source Current (Body Diode) (Note 1)			I_S	1.55	A
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface-mounted on FR4 board using the minimum recommended pad size, 2 oz. Cu.

MARKING DIAGRAM

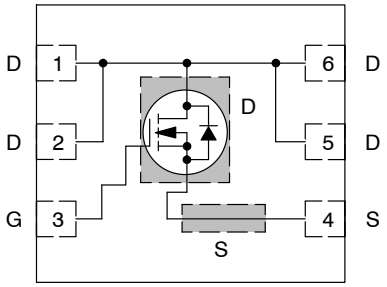


UDFN6
(μCOOL™)
CASE 517BG

AG = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

PIN CONNECTIONS



(Top View)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	81	°C/W
Junction-to-Ambient – t ≤ 5 s (Note 3)	$R_{\theta JA}$	40.5	
Junction-to-Ambient – Steady State min Pad (Note 4)	$R_{\theta JA}$	200	

3. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
4. Surface-mounted on FR4 board using the minimum recommended pad size, 2 oz. Cu.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Units
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	I_D = 250 μA, ref to 25°C			12		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 24 V	T_J = 25°C			1.0	μA
			T_J = 125°C			10	
Gate-to-Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		1.3		2.1	V
Negative Threshold Temp. Coefficient	$V_{GS(TH)}/T_J$				4.8		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 9.0 A			7.2	9	mΩ
		V_{GS} = 4.5 V, I_D = 8.0 A			9.3	12	
		V_{GS} = 3.7 V, I_D = 5.0 A			10.9	15	
		V_{GS} = 3.3 V, I_D = 5.0 A			13	19	
Forward Transconductance	g_{FS}	V_{DS} = 15 V, I_D = 9.0 A			39		S
CHARGES, CAPACITANCES & GATE RESISTANCE							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = 15 V			1172		pF
Output Capacitance	C_{OSS}				546		
Reverse Transfer Capacitance	C_{RSS}				26		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 15 V; I_D = 8.0 A			8.4		nC
Threshold Gate Charge	$Q_{G(TH)}$				1.1		
Gate-to-Source Charge	Q_{GS}				3.0		
Gate-to-Drain Charge	Q_{GD}				2.2		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 15 V; I_D = 9.0 A			18		nC
SWITCHING CHARACTERISTICS, VGS = 4.5 V (Note 6)							
Turn-On Delay Time	$t_{d(ON)}$	V_{GS} = 4.5 V, V_{DD} = 15 V, I_D = 8.0 A, R_G = 3 Ω			9.4		ns
Rise Time	t_r				15		
Turn-Off Delay Time	$t_{d(OFF)}$				14		
Fall Time	t_f				3.5		
SWITCHING CHARACTERISTICS, VGS = 10 V (Note 6)							
Turn-On Delay Time	$t_{d(ON)}$	V_{GS} = 10 V, V_{DD} = 15 V, I_D = 9.0 A, R_G = 3 Ω			6.3		ns
Rise Time	t_r				14		
Turn-Off Delay Time	$t_{d(OFF)}$				18		
Fall Time	t_f				2.4		

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Units
DRAIN-SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 1.5 A	T_J = 25°C		0.72	1.1	V
			T_J = 125°C		0.52		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dIs/dt = 100 A/μs, I_S = 1.5 A			29		ns
Charge Time	t_a				14.1		
Discharge Time	t_b				14.9		
Reverse Recovery Charge	Q_{RR}				20		nC

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

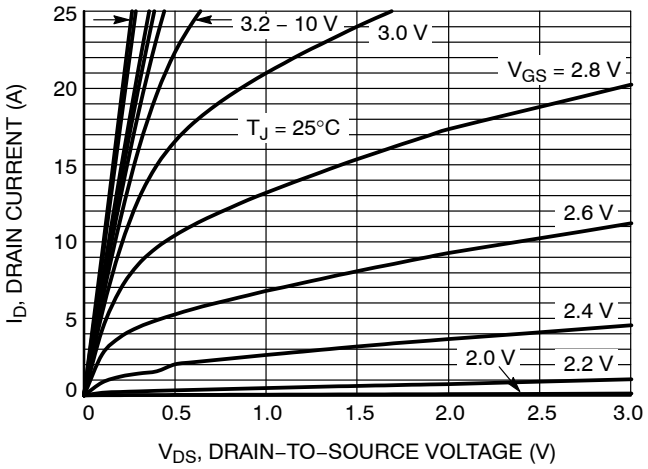


Figure 1. On–Region Characteristics

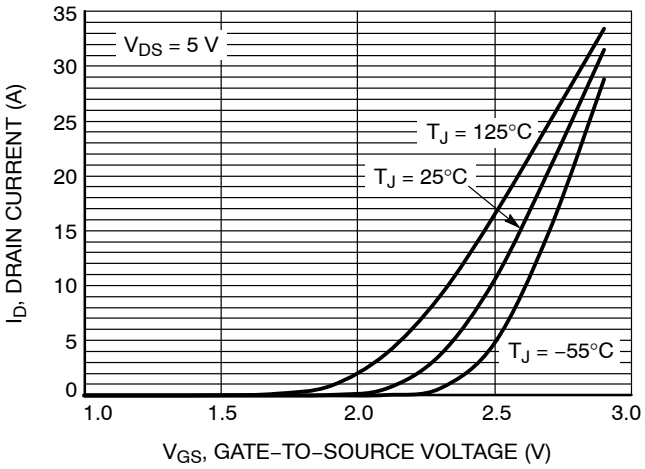


Figure 2. Transfer Characteristics

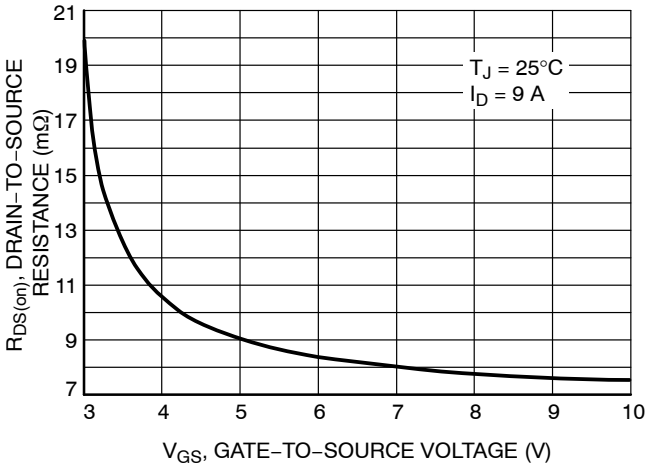


Figure 3. On–Resistance vs. Gate–to–Source Voltage

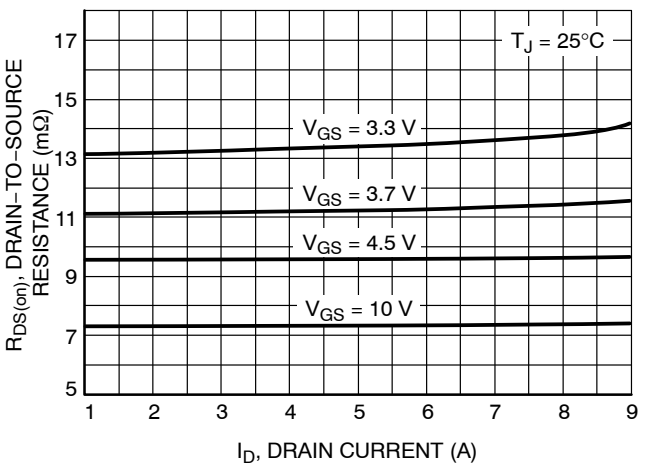


Figure 4. On–Resistance vs. Drain Current and Gate Voltage

TYPICAL CHARACTERISTICS

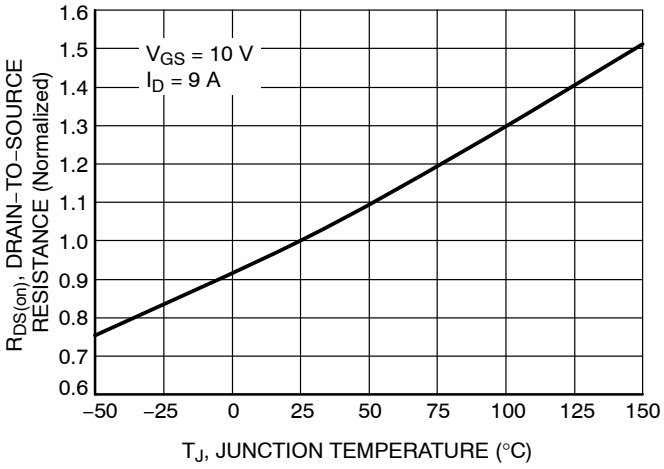


Figure 5. On−Resistance Variation with Temperature

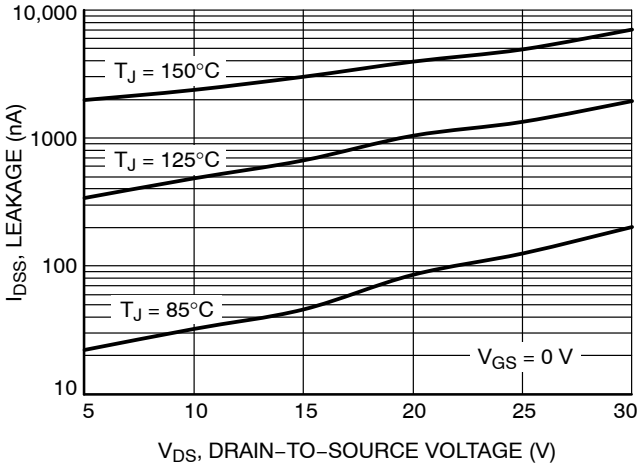


Figure 6. Drain−to−Source Leakage Current vs. Voltage

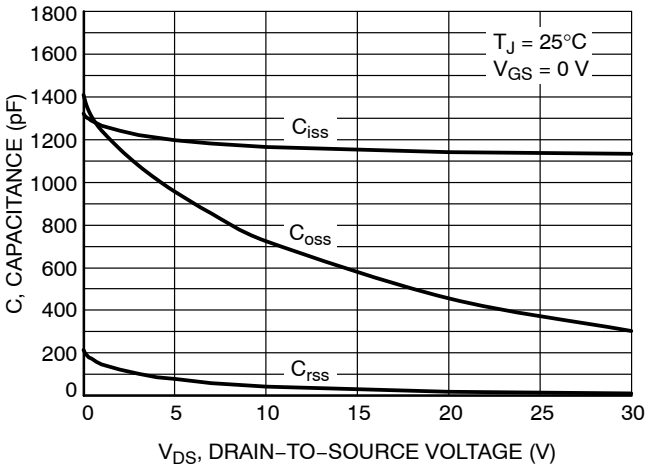


Figure 7. Capacitance Variation

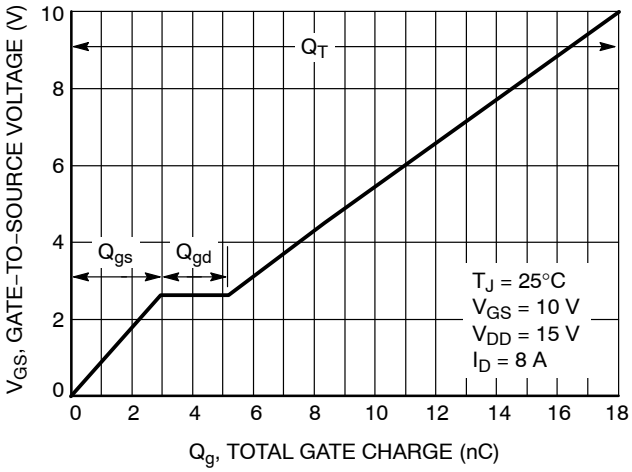


Figure 8. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

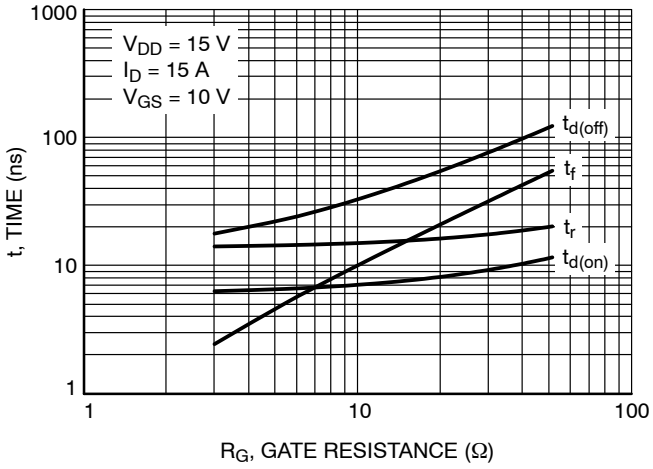


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

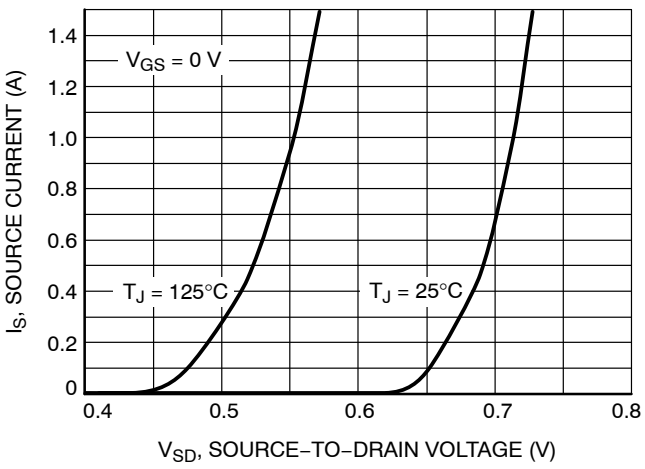


Figure 10. Diode Forward Voltage vs. Current

TYPICAL CHARACTERISTICS

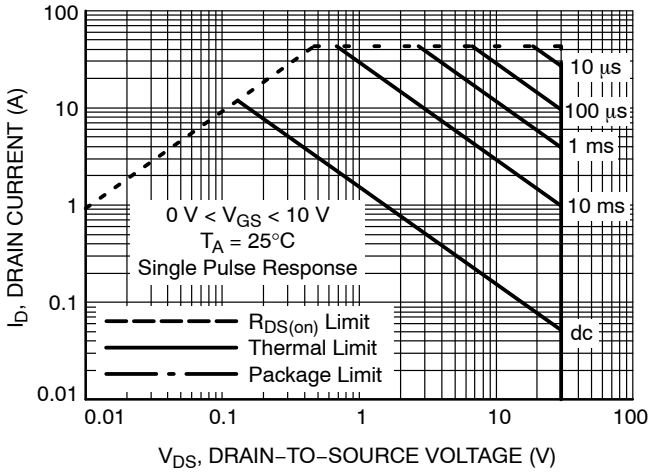


Figure 11. Maximum Rated Forward Biased Safe Operating Area

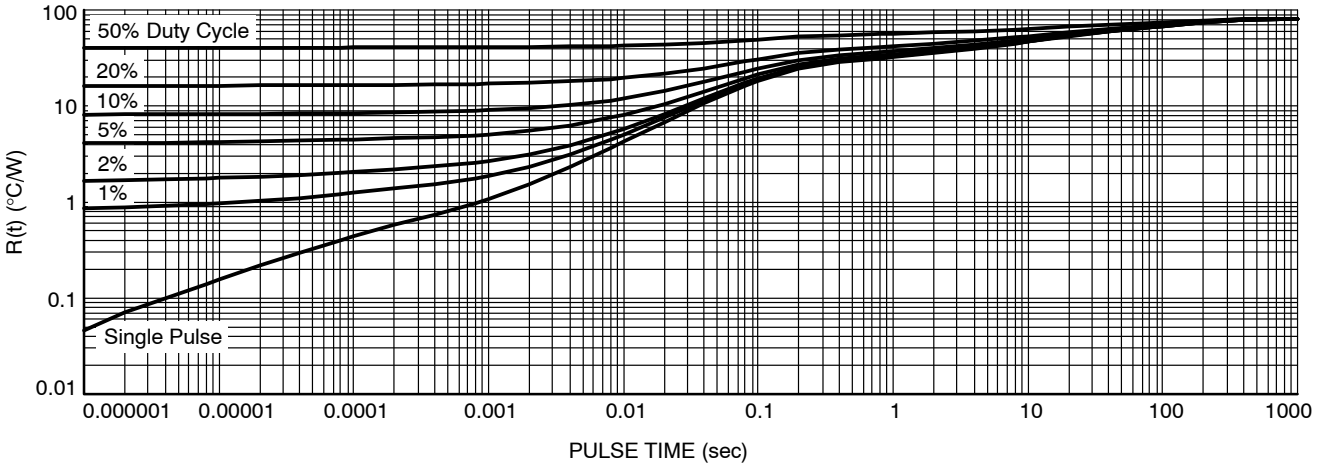


Figure 12. Thermal Response

DEVICE ORDERING INFORMATION

Device	Package	Shipping†
NTLUS4C12NTAG	UDFN6 (Pb−Free)	3000 / Tape & Reel
NTLUS4C12NTBG	UDFN6 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

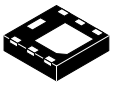
μCool is a trademark of Semiconductor Components Industries, LLC (SCILLC).

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

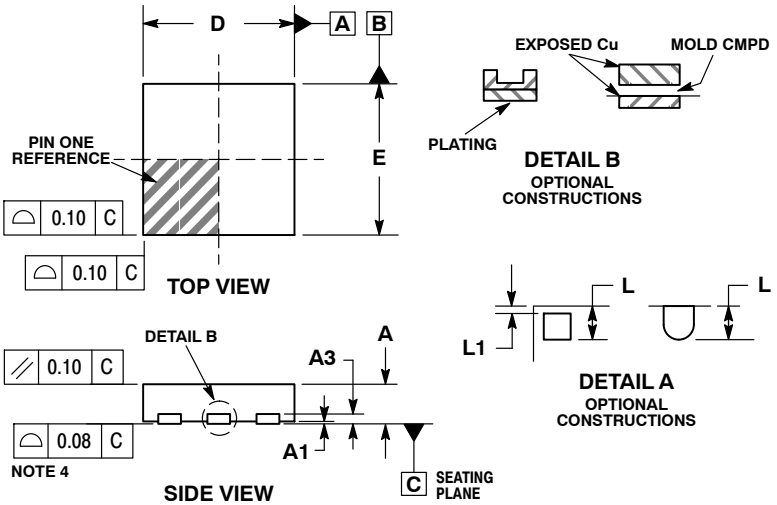
ON Semiconductor®

UDFN6 2x2, 0.65P
CASE 517BG–01
ISSUE A

DATE 04 FEB 2010

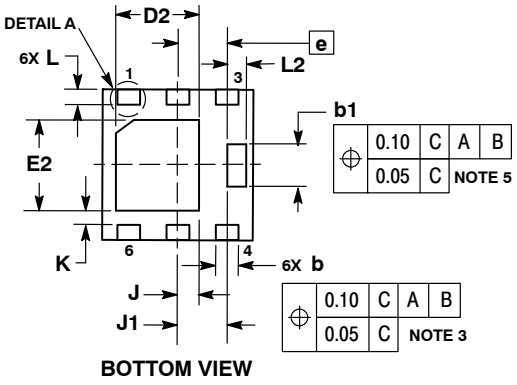


SCALE 4:1

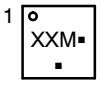


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
1. CENTER TERMINAL LEAD IS OPTIONAL. CENTER TERMINAL IS CONNECTED TO TERMINAL LEAD # 4.
2. LEADS 1, 2, 5 AND 6 ARE TIED TO THE FLAG.

	MILLIMETERS	
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.13 REF	
b	0.25	0.35
b1	0.51	0.61
D	2.00 BSC	
D2	1.00	1.20
E	2.00 BSC	
E2	1.10	1.30
e	0.65 BSC	
K	0.15 REF	
J	0.27 BSC	
J1	0.65 BSC	
L	0.20	0.30
L1	---	0.10
L2	0.20	0.30



GENERIC MARKING DIAGRAM*

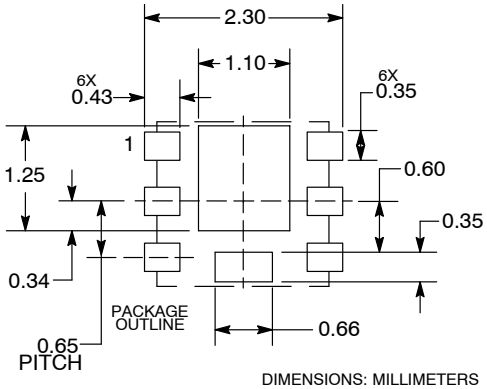


XX = Specific Device Code
M = Date Code

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, “G” or microdot “▪”, may or may not be present.

RECOMMENDED MOUNTING FOOTPRINT



DIMENSIONS: MILLIMETERS

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DESCRIPTION:	UDFN6 2X2, 0.65P	PAGE 1 OF 1

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT
North American Technical Support:
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Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:
Phone: 00421 33 790 2910
For additional information, please contact your local Sales Representative

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